

## P-Channel 2.5-V (G-S) MOSFET

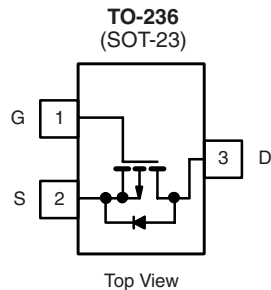
<b>PRODUCT SUMMARY</b>		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>b</sup>
- 20	0.100 at $V_{GS} = - 4.5$ V	- 2.4
	0.150 at $V_{GS} = - 2.5$ V	- 2.0

### FEATURES

- Halogen-free Option Available



**RoHS\***  
COMPLIANT



Si2301 BDS (L1)\*

\* Marking Code

**Ordering Information:** Si2301BDS-T1  
Si2301BDS-T1-E3 (Lead (Pb)-free)  
Si2301BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	- 20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>b</sup>	$I_D$	$T_A = 25$ °C	- 2.4	- 2.2	A
		$T_A = 70$ °C	- 1.9	- 1.8	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	- 10			
Continuous Source Current (Diode Conduction) <sup>b</sup>	$I_S$	- 0.72	- 0.6		
Power Dissipation <sup>b</sup>	$P_D$	$T_A = 25$ °C	0.9	0.7	W
		$T_A = 70$ °C	0.57	0.45	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

<b>THERMAL RESISTANCE RATINGS</b>				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	120	145	°C/W
Maximum Junction-to-Ambient <sup>c</sup>		140	175	

Notes:

- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 board,  $t \leq 5$  s.
- Surface Mounted on FR4 board.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.45		- 0.95	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 6			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$	- 3			
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		0.080	0.100	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		0.110	0.150	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		6.5		S
Diode Forward Voltage	$V_{SD}$	$I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$		- 0.80	- 1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}$ $I_D \cong -2.8\text{ A}$		4.5	10	nC
Gate-Source Charge	$Q_{gs}$			0.7		
Gate-Drain Charge	$Q_{gd}$			1.1		
Input Capacitance	$C_{iss}$	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		375		pF
Output Capacitance	$C_{oss}$			95		
Reverse Transfer Capacitance	$C_{rss}$			65		
<b>Switching<sup>c</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}$ $R_g = 6\text{ }\Omega$		20	30	ns
	$t_r$			40	60	
Turn-Off Time	$t_{d(off)}$			30	45	
	$t_f$			20	30	

Notes:

- a. Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .  
b. For DESIGN AID ONLY, not subject to production testing.  
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.